

N-Channel 100-V (D-S) Super Trench Power MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A) ^a	Q _g (Typ.)
100	0.0082 at V _{GS} = 10 V	15.5	27.9 nC
	0.0095 at V _{GS} = 7.5 V	14.8	
	0.0105 at V _{GS} = 6.0 V	14.0	

FEATURES

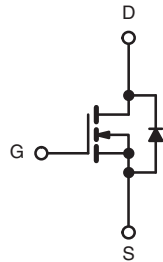
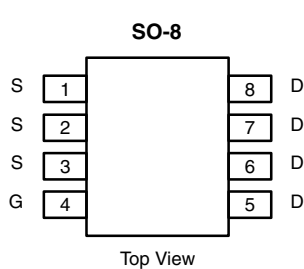
- Super Trench technology Power MOSFET
- Excellent gate charge x R_{ds (on)} product(FOM)
- Very low on-resistance R_{ds (on)}
- 100 % R_g and UIS Tested



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- DC/DC Primary Side Switch
- Telecom/Server
- Motor Drive Control
- Synchronous Rectification



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	15.5
		T _C = 70 °C	13
		T _A = 25 °C	10.2 ^{b, c}
		T _A = 70 °C	7.4 ^{b, c}
Pulsed Drain Current (t = 300 μs)	I _{DM}	70	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	3.1 ^{b, c}
Single Pulse Avalanche Current	I _{AS}	30	mJ
Avalanche Energy	E _{AS}	45	
Maximum Power Dissipation	P _D	T _C = 25 °C	7.8
		T _C = 70 °C	5
		T _A = 25 °C	3.5 ^{b, c}
		T _A = 70 °C	2.2 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	29	35	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	13	16		

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 80 °C/W.

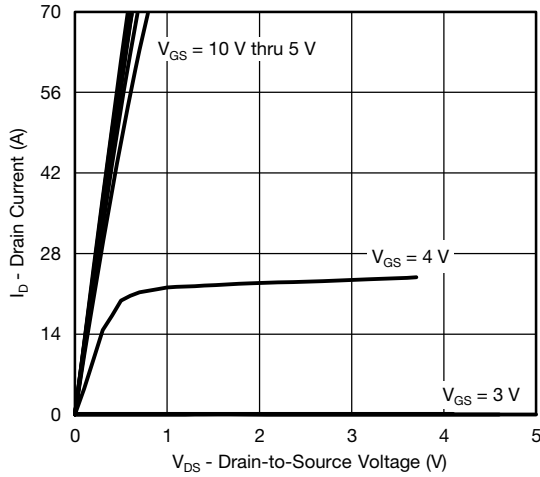
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	100			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		67		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J		- 6.4			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2		3.3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			1	μA
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A		0.0082		Ω
		V _{GS} = 7.5 V, I _D = 12 A		0.0095		
		V _{GS} = 6.0 V, I _D = 10 A		0.0105		
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 15 A		54		S
Dynamic^b						
Input Capacitance	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		3410		pF
Output Capacitance	C _{oss}		790			
Reverse Transfer Capacitance	C _{rss}		160			
Total Gate Charge	Q _g	V _{DS} = 50 V, V _{GS} = 10 V, I _D = 10 A		45.6	69	nC
		V _{DS} = 50 V, V _{GS} = 6 V, I _D = 10 A		27.9	42	
Gate-Source Charge	Q _{gs}		8.5			
Gate-Drain Charge	Q _{gd}		9.2			
Output Charge	Q _{oss}	V _{DS} = 50 V, V _{GS} = 0 V		63	95	
Gate Resistance	R _g	f = 1 MHz	0.4	1.3	2.6	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 50 V, R _L = 5 Ω I _D ≅ 10 A, V _{GEN} = 7.5 V, R _g = 1 Ω		16	32	ns
Rise Time	t _r		11	22		
Turn-Off Delay Time	t _{d(off)}		35	70		
Fall Time	t _f		10	20		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 50 V, R _L = 5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		14	28	
Rise Time	t _r		10	20		
Turn-Off Delay Time	t _{d(off)}		36	70		
Fall Time	t _f		10	20		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			7	A
Pulse Diode Forward Current ^a	I _{SM}				70	
Body Diode Voltage	V _{SD}	I _S = 5 A		0.75	1.1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C		49	95	ns
Body Diode Reverse Recovery Charge	Q _{rr}		58	115	nC	
Reverse Recovery Fall Time	t _a		21		ns	
Reverse Recovery Rise Time	t _b		28			

Notes:

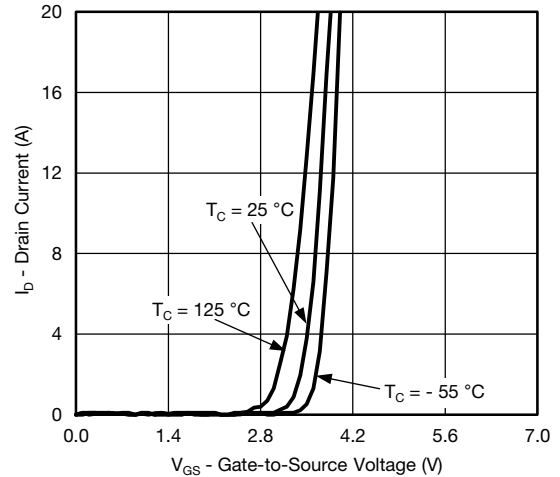
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

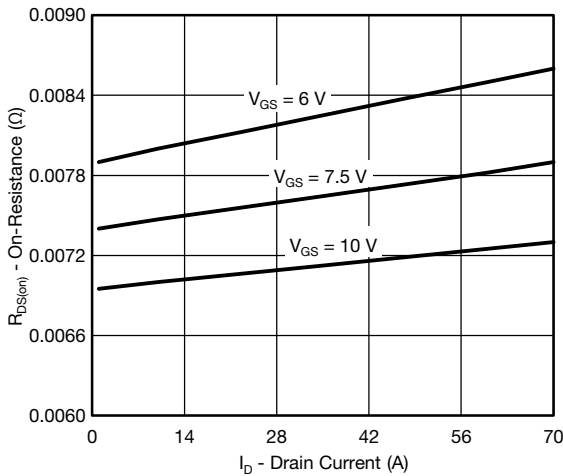
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



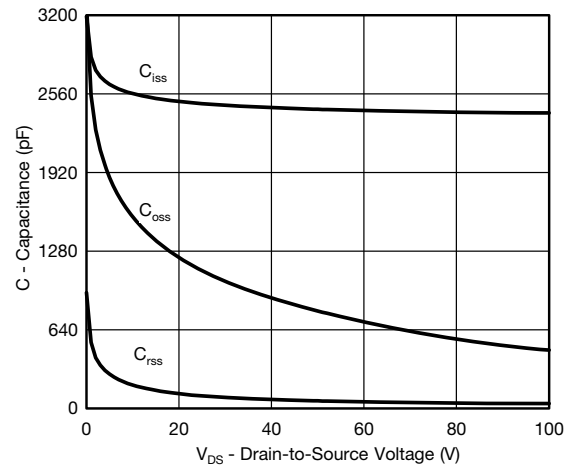
Output Characteristics



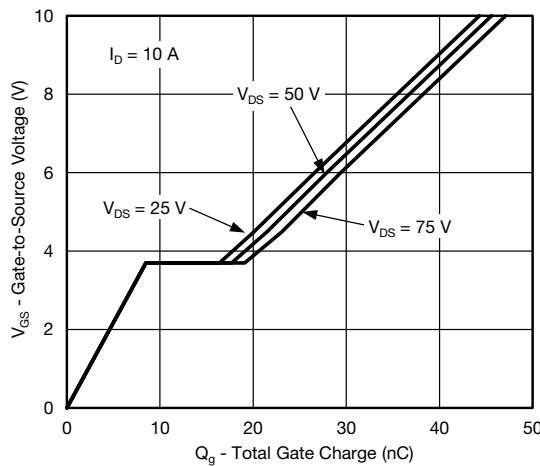
Transfer Characteristics



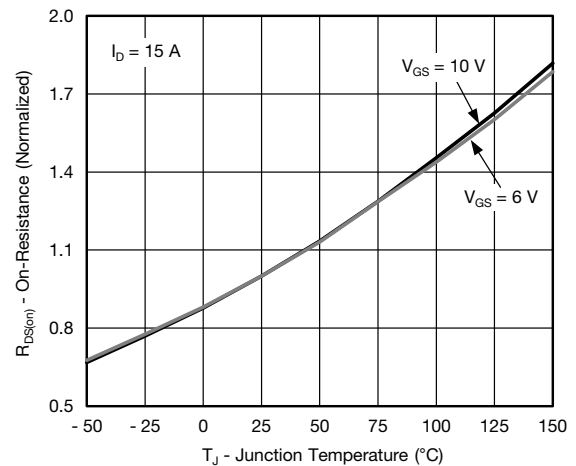
On-Resistance vs. Drain Current



Capacitance

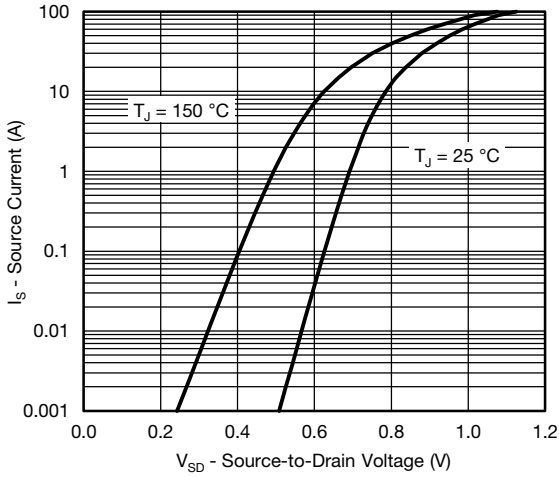


Gate Charge

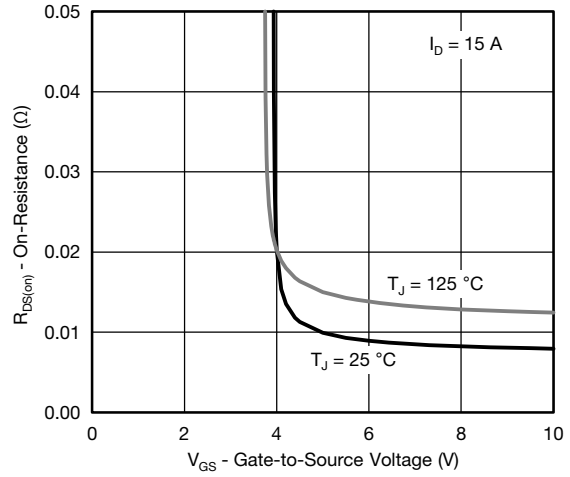


On-Resistance vs. Junction Temperature

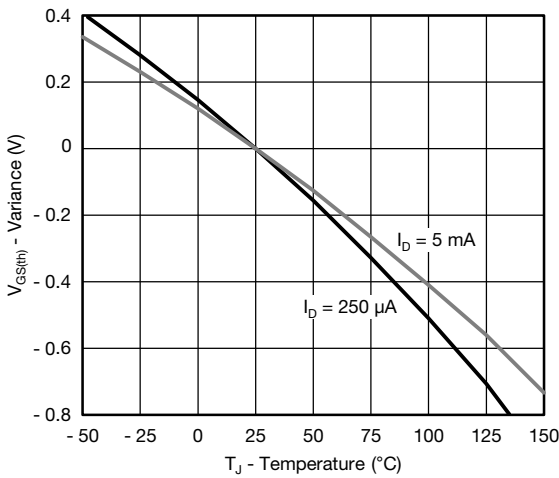
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



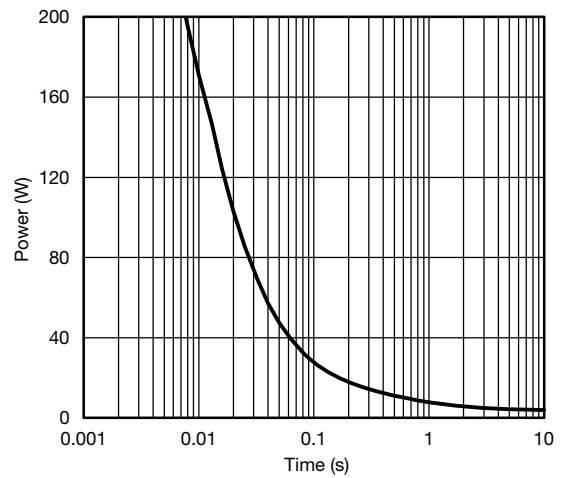
Source-Drain Diode Forward Voltage



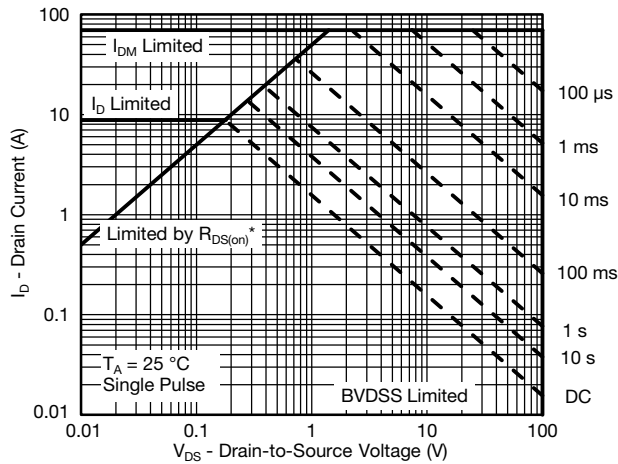
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



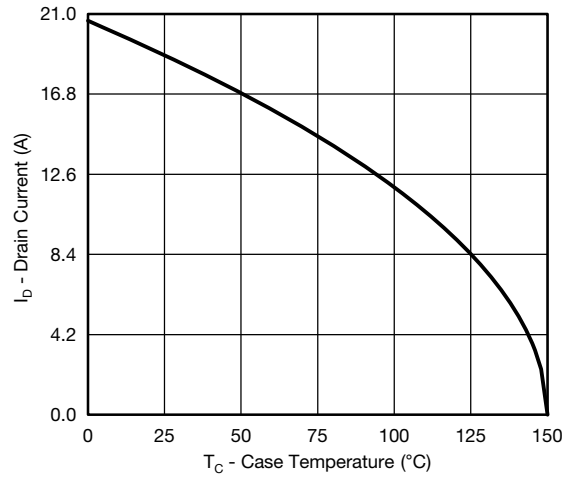
Single Pulse Power, Junction-to-Ambient



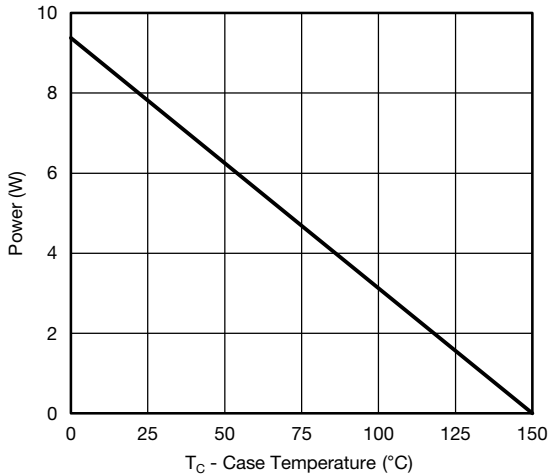
Safe Operating Area, Junction-to-Ambient

* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

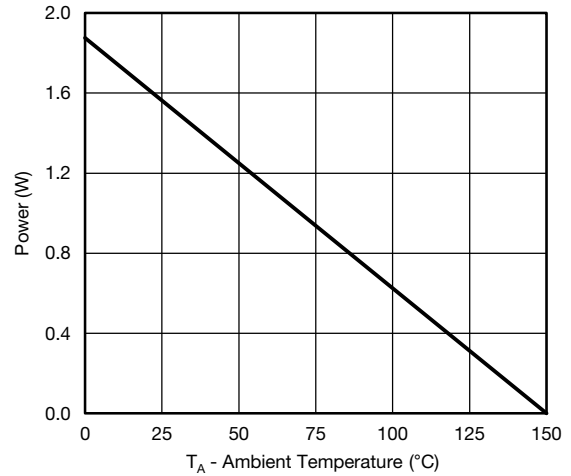
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



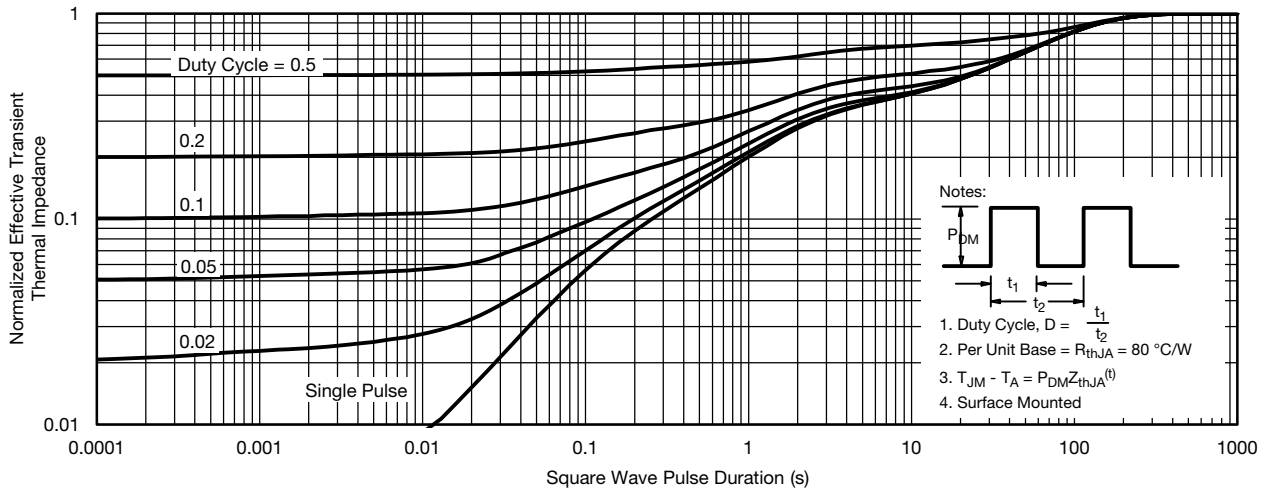
Power, Junction-to-Foot



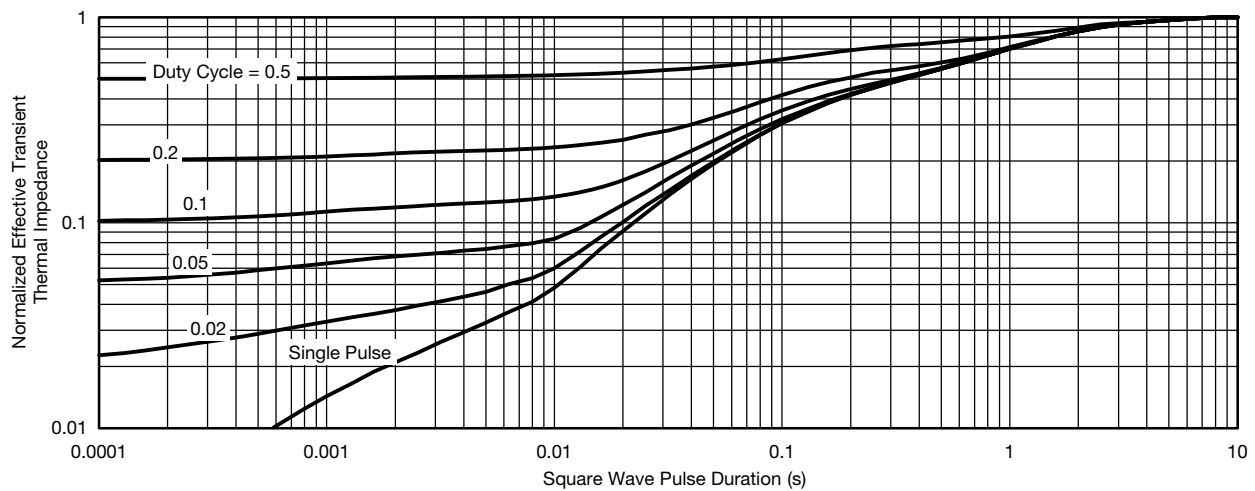
Power, Junction-to-Ambient

* The power dissipation P_D is based on T_{J(max)} = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



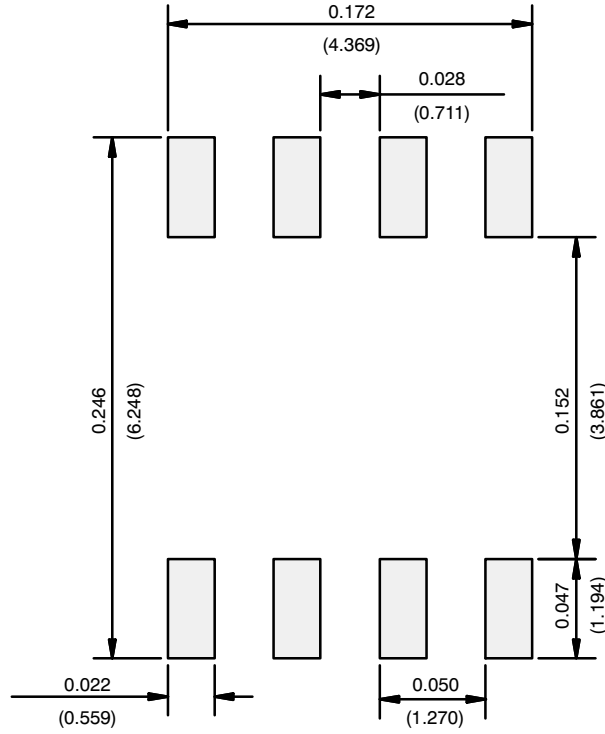
Normalized Thermal Transient Impedance, Junction-to-Foot

SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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